



10 A, 200V - 600 V Surface Mount Ultrafast Rectifiers

FEATURES

- Very Low Profile: Typical Height of 1.1 mm
- Ultrafast Recovery Time
- Low Forward Voltage Drop
- Low Thermal Resistance
- Very Stable Operation at Industrial Temperature, 150°C
- RoHS Compliant
- Green Molding Compound as per IEC61249 Standard
- Lead Free in Compliance with EU RoHS 2011/65/EU Directive
- With DAP Option Only

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage TES10D TES10G TES10J	V _{RRM}	200 400 600	V
Average Forward Rectified Current	I _{F(AV)}	10	A
Peak Forward Surge Current: 8.3 ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM}	150	A
Operating Junction Temperature Range	T _J	-55 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Values are at T_A = 25°C unless otherwise noted) (Note 1)

Parameter	Symbol	Value	Unit
Thermal Characteristics, Junction-to-Lead, Thermocouple Soldered to Cathode	Ψ _{JL}	6	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	100	°C/W

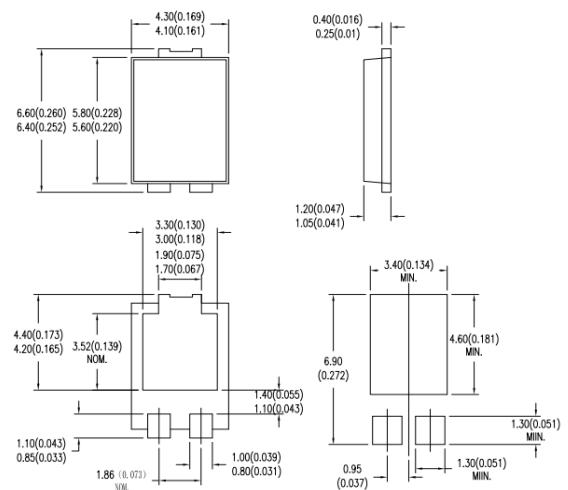
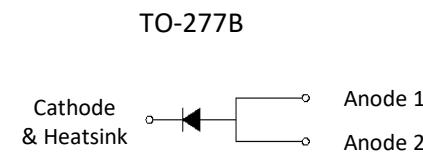
1. Per JESD51-3 Recommended Thermal Test Board.

ELECTRICAL CHARACTERISTICS (Values are at T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Value			Unit
			TES10D	TES10G	TES10J	
V _F	Maximum Instantaneous Forward Voltage (Note 2)	I _F = 10 A	0.95	1.30	1.80	V
I _R	Maximum Reverse Current at Rated V _R	T _J = 25°C	5			μA
		T _J = 125°C	250	500		
C _J	Typical Junction Capacitance	V _R = 4 V, f = 1 MHz	140			pF
T _{rr}	Typical Reverse Recovery Time	I _F = 0.5 A, I _R = 1 A, I _{RR} = 0.25 A	35			ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse test with PW = 300 μs, 1% duty cycle





TYPICAL CHARACTERISTICS

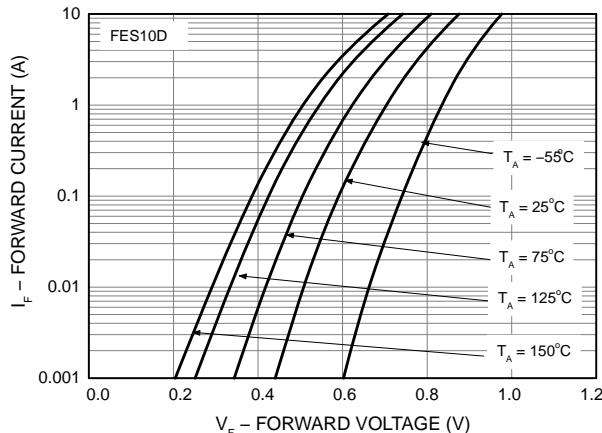


Fig 1. Typical Forward Characteristics for FES10D

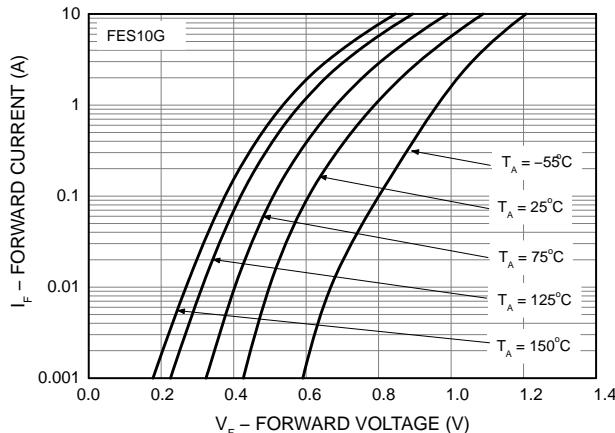


Fig 2. Typical Forward Characteristics for FES10G

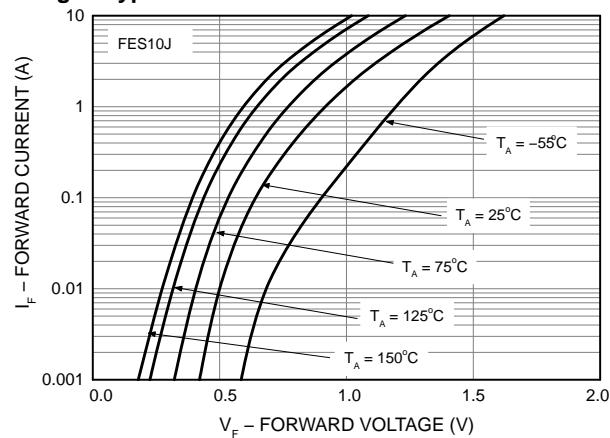


Fig 3. Typical Forward Characteristics for FES10J

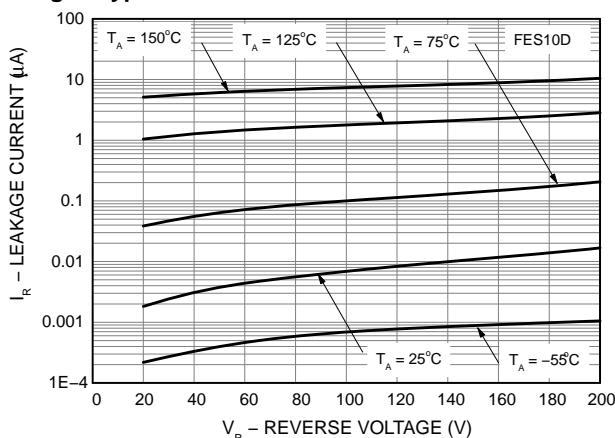


Fig 4. Typical Reverse Characteristics for FES10D

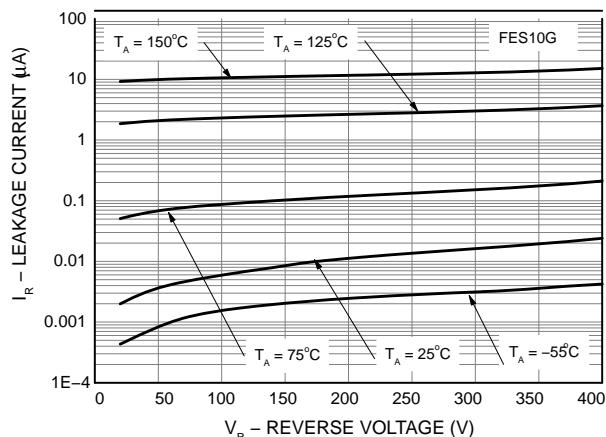


Fig 5. Typical Reverse Characteristics for FES10G

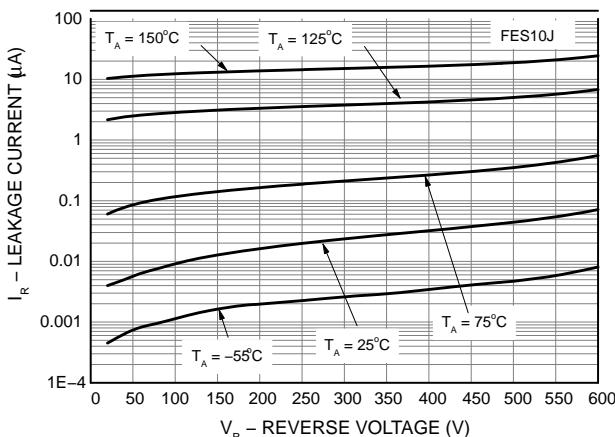


Fig 6. Typical Reverse Characteristics for FES10J

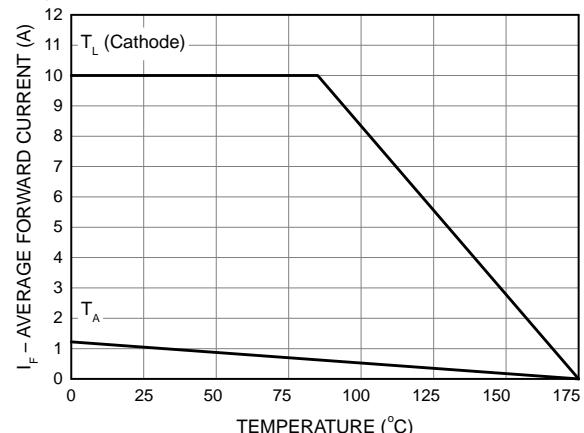


Fig 7. Forward Current Derating Curve

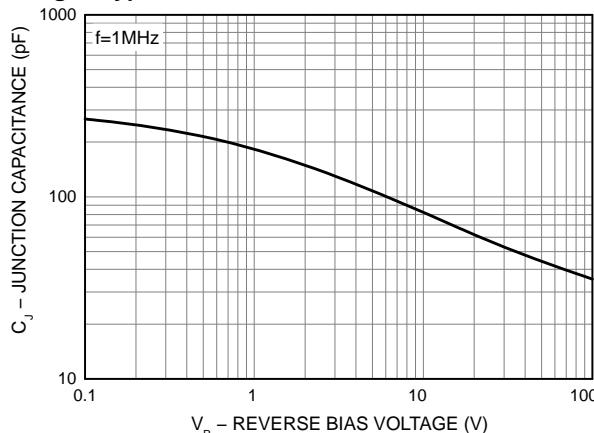


Fig 8. Typical Junction Capacitance